

L Number	Hits	Search Text	DB	Time stamp
-	12	((("3932226") or ("4503451") or ("4670297") or ("4857481") or ("4939567") or ("4977439") or ("5158986") or ("5202754") or ("5227658") or ("5232866") or ("5268315") or ("5270261"))).PN.	USPAT	2002/02/20 09:31
-	18	((("5308440") or ("5334356") or ("5349743") or ("5382832") or ("5396093") or ("5410169") or ("5436173") or ("5438009") or ("5497017") or ("5504357") or ("5539227") or ("5593921") or ("5705425") or ("5747867") or ("5798544") or ("5892707") or ("5930596") or ("5930668"))).PN.	USPAT	2002/02/19 17:49
-	1	("6025261").PN.	USPAT	2002/02/20 09:32
-	54674	257/\$.ccls.	USPAT	2002/02/20 09:33
-	44983	438/\$.ccls.	USPAT	2002/02/20 09:33
-	10840	216/\$.ccls.	USPAT	2002/02/20 09:33
-	29455	(216/\$.ccls. 257/\$.ccls. 438/\$.ccls. ) and ((opening\$1 hole\$1 groove\$1 recess\$3 trench\$2 aperture\$1) near10 (si silicon semiconductor\$3))	USPAT	2002/02/20 11:38
-	2950	((216/\$.ccls. 257/\$.ccls. 438/\$.ccls. ) and ((opening\$1 hole\$1 groove\$1 recess\$3 trench\$2 aperture\$1) near10 (si silicon semiconductor\$3))) and ((burie\$1 bury\$3 embedd\$3) near2 (contact\$1 conduct\$3 wire\$1 wiring\$1 connect\$3))	USPAT	2002/02/20 11:42
-	2607	((216/\$.ccls. 257/\$.ccls. 438/\$.ccls. ) and ((opening\$1 hole\$1 groove\$1 recess\$3 trench\$2 aperture\$1) near10 (si silicon semiconductor\$3))) and ((burie\$1 bury\$3 embedd\$3) near2 (contact\$1 conduct\$3 wire\$1 wiring\$1 connect\$3)) ) and (deep depth shallow level\$1 distance\$1 )	USPAT	2002/02/20 11:44
-	409	((216/\$.ccls. 257/\$.ccls. 438/\$.ccls. ) and ((opening\$1 hole\$1 groove\$1 recess\$3 trench\$2 aperture\$1) near10 (si silicon semiconductor\$3))) and ((burie\$1 bury\$3 embedd\$3) near2 (contact\$1 conduct\$3 wire\$1 wiring\$1 connect\$3)) ) and (deep depth shallow level\$1 distance\$1 ) and ((oxidation oxidid\$4) near5 (wall\$1 sidewall\$1 bottom lin\$3 protect\$3))	USPAT	2002/02/20 16:33
-	409	((216/\$.ccls. 257/\$.ccls. 438/\$.ccls. ) and ((opening\$1 hole\$1 groove\$1 recess\$3 trench\$2 aperture\$1) near10 (si silicon semiconductor\$3))) and ((burie\$1 bury\$3 embedd\$3) near2 (contact\$1 conduct\$3 wire\$1 wiring\$1 connect\$3)) ) and (deep depth shallow level\$1 distance\$1 ) and ((oxidation oxidid\$4) near5 (wall\$1 sidewall\$1 bottom lin\$3 protect\$3))	USPAT	2002/02/20 16:39